

Description

The IRFR5305TRPBF uses advanced trench technologyto provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

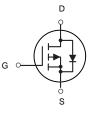
 $V_{DS} = -60V, I_D = -20A$ $R_{DS(ON)} < 72m\Omega @ V_{GS} = -10V$ $R_{DS(ON)} < 100m\Omega @ V_{GS} = -4.5V$

Application

PWM applications Load switch Power management







P-Channel MOSFET

Package Marking and Ordering Information

0 0	0		
Product ID	Pack	Marking	Qty(PCS)
IRFR5305TRPBF	TO252-2L	20P06 XXYY	2500

ABSOLUTE MAXIMUM RATINGS(TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-60	V
VGS	Gate-Source Voltage	±20	V
I₀(25°C)		-20	А
I⊳(70°C)	Drain Current-Continuous@ Current-Pulsed (Note 1)	-15	А
IDM		-48	А
Po	Maximum Power Dissipation	40	W
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 175	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	20	°C /W



P-Channel Enhancement Mode MOSFET

ELECTRICAL CHARACTERISTICS (TA=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Мах	Unit
Drain-Source Breakdown Voltage	BVDSS	V _{GS} =0V I _D =-250µA	-60			V
Zero Gate Voltage Drain Current	loss	V _{DS} =-48V,V _{GS} =0V			-1	μA
Gate-Body Leakage Current	lgss	V _{GS} =±20V,V _{DS} =0V			±100	nA
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} , I _D =-250µA	-1	-1.8	-2.5	V
		V _{GS} =-10V, I _D =-10A		64	72	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =-4.5V, I _D =-10A		90	100	mΩ
Forward Transconductance	g FS	V _{DS} =-5V, I _D =-20A	5			S
Input Capacitance	Clss			2460		PF
Output Capacitance	Coss	V _{DS} =-30V,V _{GS} =0V, F=1.0MHz		220		PF
Reverse Transfer Capacitance	Crss			155		PF
Turn-on Delay Time	td(on)			14		nS
Turn-on Rise Time	tr	V _{DS} =-30V,V _{GS} =-		20		nS
Turn-Off Delay Time	td(off)	- 10V,R _{GEN} =3Ω I _D =1A		40		nS
Turn-Off Fall Time	t _f	-		19		nS
Total Gate Charge	Qg			48		nC
Gate-Source Charge	Qgs	V _{DS} =-30V, I _D =-20A, V _{GS} =-10V		11		nC
Gate-Drain Charge	Qgd			10		nC
Body Diode Reverse Recovery Time	T _{rr}	l⊧=-20A, dl/dt=100A/µs		40		nS
Body Diode Reverse Recovery Charge	Qrr			56		nC
Diode Forward Voltage (Note 3)	Vsd	V _{GS} =0V,I _S =-1A		-0.72	-1	V

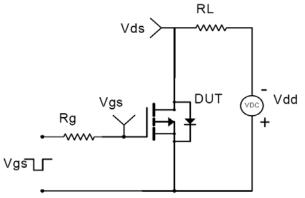
NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Surface Mounted on 1in² FR4 Board, t ≤ 10 sec.
 Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%. 4. Guaranteed by design, not subject to production testing.



TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



10%

Figure 1:Switching Test Circuit

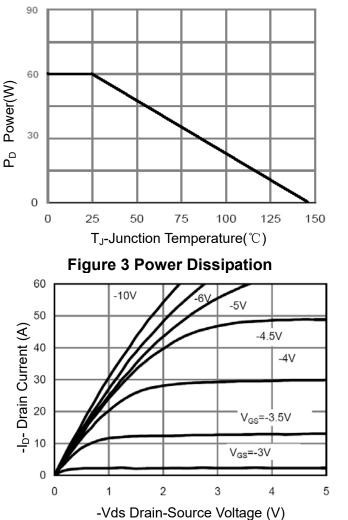


Figure 5 Output CHARACTERISTICS

t_{d(on)} t_{d(off)} INVERTED Vout 10% 10 90% VIN 509 PULSE WIDTH

Figure 2:Switching Waveforms

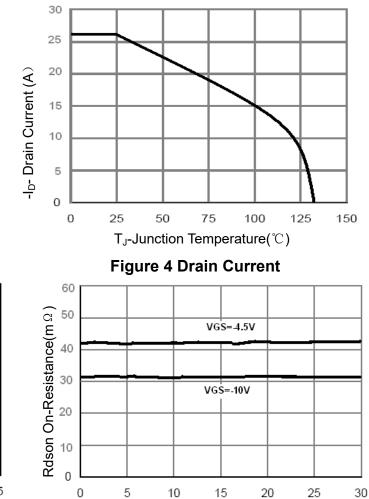
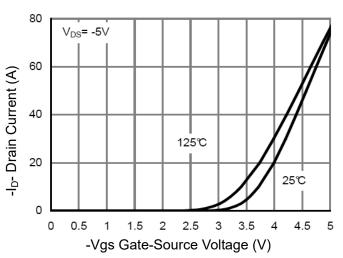


Figure 6 Drain-Source On-Resistance

-I_D- Drain Current (A)







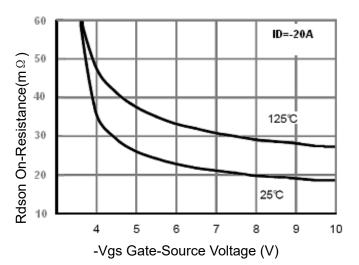
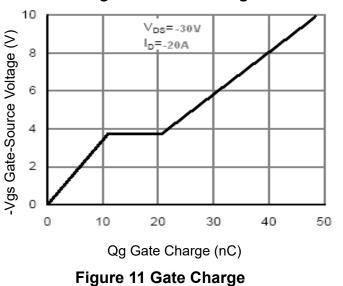


Figure 9 Rdson vs Vgs



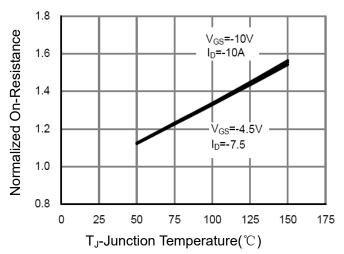
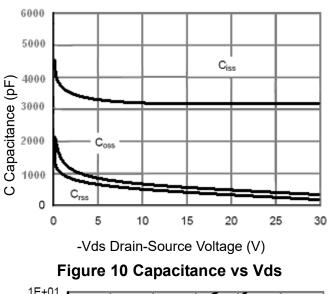


Figure 8 Drain-Source On-Resistance



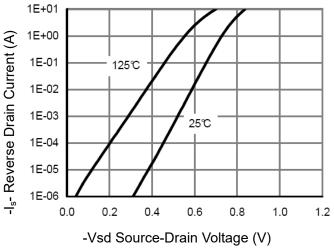


Figure 12 Source- Drain Diode Forward



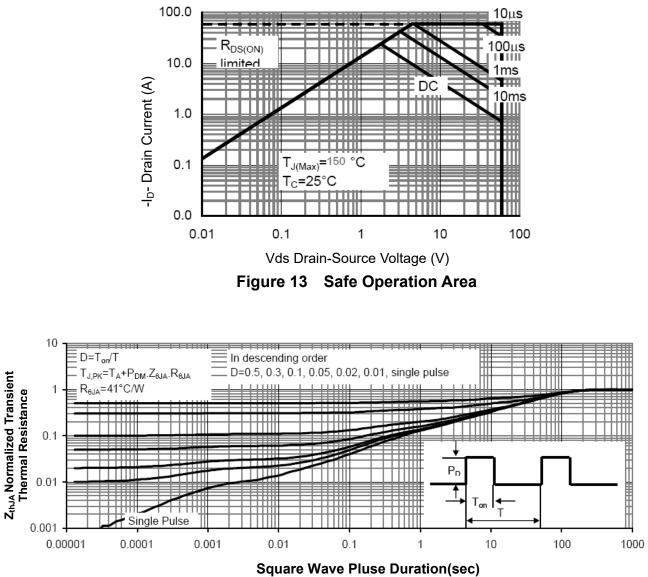
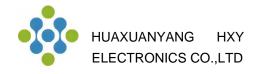
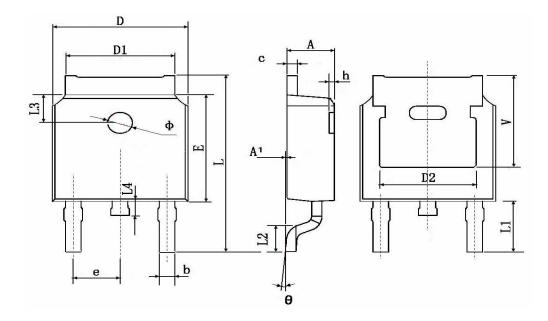


Figure 14 Normalized Maximum Transient Thermal Impedance



TO252-2L Package Information



	Dimensions In Millimeters		Dimensions In Inches			
Symbol	Min.	Max.	Min.	Max.		
A	2.200	2.400	0.087	0.094		
A1	0.000	0.127	0.000	0.005		
b	0.660	0.860	0.026	0.034		
С	0.460	0.580	0.018	0.023		
D	6.500	6.700	0.256	0.264		
D1	5.100	5.460	0.201	0.215		
D2	4.830 TYP.		0.190 TYP.			
E	6.000	6.200	0.236	0.244		
е	2.186	2.386	0.086	0.094		
L	9.800	10.400	0.386	0.409		
L1	2.900	2.900 TYP.		0.114 TYP.		
L2	1.400	1.700	0.055	0.067		
L3) TYP.		B TYP.		
L4	0.600	1.000	0.024	0.039		
Φ	1.100	1.300	0.043	0.051		
θ	0 °	8°	0°	8°		
h	0.000	0.300	0.000	0.012		
V	5.350) TYP.	0.211 TYP.			



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